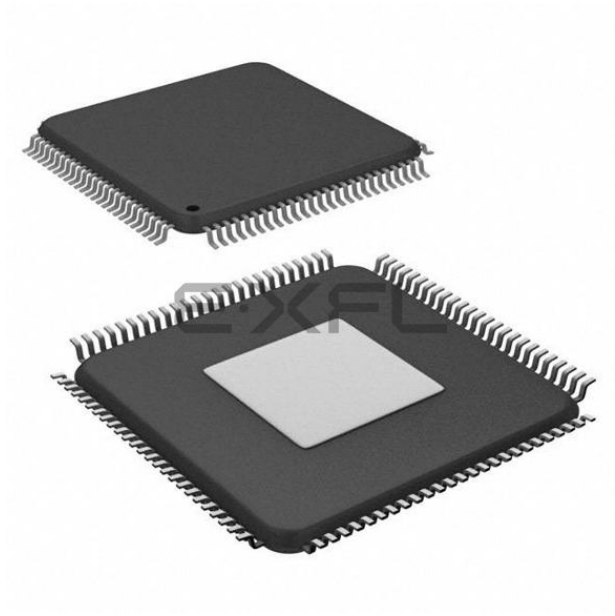
Infineon Technologies - XC2263N24F40LAAKXUMA1 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16/32-Bit
Speed	40MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	76
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	26K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xc2263n24f40laakxuma1

Table 5 Interface Channel Association

Total Number	Available Channels / Message Objects
6 CAN nodes	CAN0, CAN1, CAN2,CAN3, CAN4, CAN5 256 message objects
2 serial channels	U0C0, U0C1
4 serial channels	U0C0, U0C1, U1C0, U1C1
6 serial channels	U0C0, U0C1, U1C0, U1C1, U2C0, U2C1

The XC226xN types are offered with several SRAM memory sizes. **Figure 1** shows the allocation rules for PSRAM and DSRAM. Note that the rules differ:

- PSRAM allocation starts from the **lower** address
- DSRAM allocation starts from the **higher** address

For example 8 Kbytes of PSRAM will be allocated at E0’0000h-E0’1FFFh and 8 Kbytes of DSRAM will be at 00’C000h-00’DFFFh.

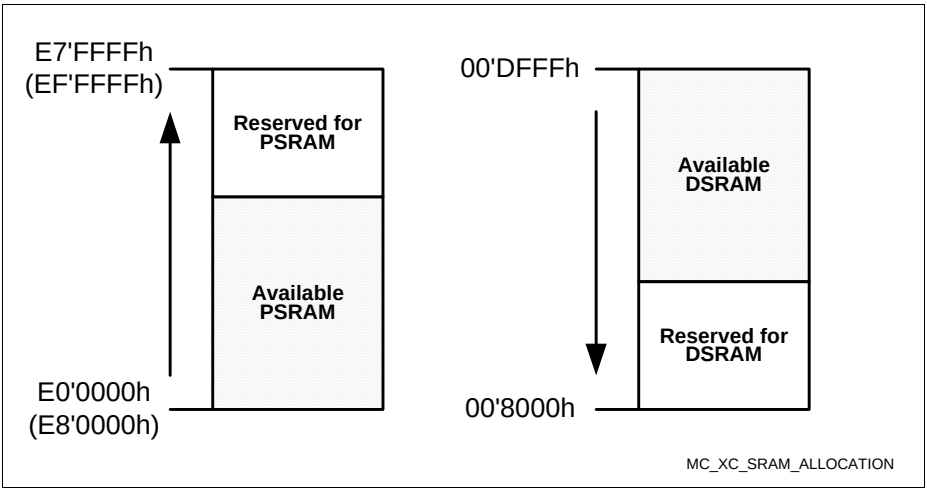

Figure 1 SRAM Allocation

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
9	P7.4	O0 / I	St/B	**Bit 4 of Port 7, General Purpose Input/Output**
	EMUX2	O1	St/B	**External Analog MUX Control Output 2 (ADC1)**
	U0C1_DOUT	O2	St/B	**USIC0 Channel 1 Shift Data Output**
	U0C1_SCLKOUT	O3	St/B	**USIC0 Channel 1 Shift Clock Output**
	TCK_C	IH	St/B	**DAP0/JTAG Clock Input** If JTAG pos. C is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it. If DAP pos. 2 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.
	U0C0_DX0D	I	St/B	**USIC0 Channel 0 Shift Data Input**
	U0C1_DX1E	I	St/B	**USIC0 Channel 1 Shift Clock Input**
11	P6.0	O0 / I	DA/A	**Bit 0 of Port 6, General Purpose Input/Output**
	EMUX0	O1	DA/A	**External Analog MUX Control Output 0 (ADC0)**
	TxDC2	O2	DA/A	**CAN Node 2 Transmit Data Output**
	$\overline{\text{BRKOUT}}$	O3	DA/A	**OCDS Break Signal Output**
	ADCx_REQGTyG	I	DA/A	**External Request Gate Input for ADC0/1**
	U1C1_DX0E	I	DA/A	**USIC1 Channel 1 Shift Data Input**
12	P6.1	O0 / I	DA/A	**Bit 1 of Port 6, General Purpose Input/Output**
	EMUX1	O1	DA/A	**External Analog MUX Control Output 1 (ADC0)**
	T3OUT	O2	DA/A	**GPT12E Timer T3 Toggle Latch Output**
	U1C1_DOUT	O3	DA/A	**USIC1 Channel 1 Shift Data Output**
	ADCx_REQTRyE	I	DA/A	**External Request Trigger Input for ADC0/1**
	RxDC2E	I	DA/A	**CAN Node 2 Receive Data Input**
	ESR1_6	I	DA/A	**ESR1 Trigger Input 6**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
24	P5.3	I	In/A	**Bit 3 of Port 5, General Purpose Input**
	ADC0_CH3	I	In/A	**Analog Input Channel 3 for ADC0**
	T3INA	I	In/A	**GPT12E Timer T3 Count/Gate Input**
28	P5.4	I	In/A	**Bit 4 of Port 5, General Purpose Input**
	ADC0_CH4	I	In/A	**Analog Input Channel 4 for ADC0**
	T3EUDA	I	In/A	**GPT12E Timer T3 External Up/Down Control Input**
	TMS_A	I	In/A	**JTAG Test Mode Selection Input**
29	P5.5	I	In/A	**Bit 5 of Port 5, General Purpose Input**
	ADC0_CH5	I	In/A	**Analog Input Channel 5 for ADC0**
	CCU60_T12HRB	I	In/A	**External Run Control Input for T12 of CCU60**
30	P5.8	I	In/A	**Bit 8 of Port 5, General Purpose Input**
	ADC0_CH8	I	In/A	**Analog Input Channel 8 for ADC0**
	ADC1_CH8	I	In/A	**Analog Input Channel 8 for ADC1**
	CCU6x_T12HRC	I	In/A	**External Run Control Input for T12 of CCU60/1**
	CCU6x_T13HRC	I	In/A	**External Run Control Input for T13 of CCU60/1**
	U2C0_DX0F	I	In/A	**USIC2 Channel 0 Shift Data Input**
31	P5.9	I	In/A	**Bit 9 of Port 5, General Purpose Input**
	ADC0_CH9	I	In/A	**Analog Input Channel 9 for ADC0**
	ADC1_CH9	I	In/A	**Analog Input Channel 9 for ADC1**
	CC2_T7IN	I	In/A	**CAPCOM2 Timer T7 Count Input**
32	P5.10	I	In/A	**Bit 10 of Port 5, General Purpose Input**
	ADC0_CH10	I	In/A	**Analog Input Channel 10 for ADC0**
	ADC1_CH10	I	In/A	**Analog Input Channel 10 for ADC1**
	$\overline{\text{BRKIN\_A}}$	I	In/A	**OCDS Break Signal Input**
	U2C1_DX0F	I	In/A	**USIC2 Channel 1 Shift Data Input**
	CCU61_T13HRA	I	In/A	**External Run Control Input for T13 of CCU61**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
49	P4.3	O0 / I	St/B	**Bit 3 of Port 4, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	CC2_CC27	O3 / I	St/B	**CAPCOM2 CC27IO Capture Inp./ Compare Out.**
	$\overline{CS3}$	OH	St/B	**External Bus Interface Chip Select 3 Output**
	RxDC2A	I	St/B	**CAN Node 2 Receive Data Input**
	T2EUDA	I	St/B	**GPT12E Timer T2 External Up/Down Control Input**
53	P0.0	O0 / I	St/B	**Bit 0 of Port 0, General Purpose Input/Output**
	U1C0_DOUT	O1	St/B	**USIC1 Channel 0 Shift Data Output**
	CCU61_CC60	O3	St/B	**CCU61 Channel 0 IOutput**
	A0	OH	St/B	**External Bus Interface Address Line 0**
	U1C0_DX0A	I	St/B	**USIC1 Channel 0 Shift Data Input**
	CCU61_CC60INA	I	St/B	**CCU61 Channel 0 Input**
	ESR1_11	I	St/B	**ESR1 Trigger Input 11**
54	P2.7	O0 / I	St/B	**Bit 7 of Port 2, General Purpose Input/Output**
	U0C1_SELO0	O1	St/B	**USIC0 Channel 1 Select/Control 0 Output**
	U0C0_SELO1	O2	St/B	**USIC0 Channel 0 Select/Control 1 Output**
	CC2_CC20	O3 / I	St/B	**CAPCOM2 CC20IO Capture Inp./ Compare Out.**
	A20	OH	St/B	**External Bus Interface Address Line 20**
	U0C1_DX2C	I	St/B	**USIC0 Channel 1 Shift Control Input**
	RxDC1C	I	St/B	**CAN Node 1 Receive Data Input**
	ESR2_7	I	St/B	**ESR2 Trigger Input 7**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
78	P1.0	O0 / I	St/B	**Bit 0 of Port 1, General Purpose Input/Output**
	U1C0_MCLKOUT	O1	St/B	**USIC1 Channel 0 Master Clock Output**
	U1C0_SELO4	O2	St/B	**USIC1 Channel 0 Select/Control 4 Output**
	A8	OH	St/B	**External Bus Interface Address Line 8**
	ESR1_3	I	St/B	**ESR1 Trigger Input 3**
	T6INB	I	St/B	**GPT12E Timer T6 Count/Gate Input**
79	P10.8	O0 / I	St/B	**Bit 8 of Port 10, General Purpose Input/Output**
	U0C0_MCLKOUT	O1	St/B	**USIC0 Channel 0 Master Clock Output**
	U0C1_SELO0	O2	St/B	**USIC0 Channel 1 Select/Control 0 Output**
	U2C1_DOUT	O3	St/B	**USIC2 Channel 1 Shift Data Output**
	AD8	OH / IH	St/B	**External Bus Interface Address/Data Line 8**
	CCU60_CCPOS1A	I	St/B	**CCU60 Position Input 1**
	U0C0_DX1C	I	St/B	**USIC0 Channel 0 Shift Clock Input**
	$\overline{\text{BRKIN\_B}}$	I	St/B	**OCDS Break Signal Input**
	T3EUDB	I	St/B	**GPT12E Timer T3 External Up/Down Control Input**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
97	$\overline{\text{PORST}}$	I	In/B	**Power On Reset Input** A low level at this pin resets the XC226xN completely. A spike filter suppresses input pulses <10 ns. Input pulses >100 ns safely pass the filter. The minimum duration for a safe recognition should be 120 ns. An internal pull-up device will hold this pin high when nothing is driving it.
98	$\overline{\text{ESR1}}$	O0 / I	St/B	**External Service Request 1** After power-up, an internal weak pull-up device holds this pin high when nothing is driving it.
	RxDC0E	I	St/B	**CAN Node 0 Receive Data Input**
	U1C0_DX0F	I	St/B	**USIC1 Channel 0 Shift Data Input**
	U1C0_DX2C	I	St/B	**USIC1 Channel 0 Shift Control Input**
	U1C1_DX0C	I	St/B	**USIC1 Channel 1 Shift Data Input**
	U1C1_DX2B	I	St/B	**USIC1 Channel 1 Shift Control Input**
	U2C1_DX2C	I	St/B	**USIC2 Channel 1 Shift Control Input**
99	$\overline{\text{ESR0}}$	O0 / I	St/B	**External Service Request 0** After power-up, $\overline{\text{ESR0}}$ operates as open-drain bidirectional reset with a weak pull-up.
	U1C0_DX0E	I	St/B	**USIC1 Channel 0 Shift Data Input**
	U1C0_DX2B	I	St/B	**USIC1 Channel 0 Shift Control Input**
10	V_{DDIM}	-	PS/M	**Digital Core Supply Voltage for Domain M** Decouple with a ceramic capacitor, see Data Sheet for details.
38, 64, 88	V_{DDI1}	-	PS/1	**Digital Core Supply Voltage for Domain 1** Decouple with a ceramic capacitor, see Data Sheet for details. All V_{DDI1} pins must be connected to each other.
14	V_{DDPA}	-	PS/A	**Digital Pad Supply Voltage for Domain A** Connect decoupling capacitors to adjacent V_{DDP}/V_{SS} pin pairs as close as possible to the pins. *Note: The A/D_Converters and ports P5, P6 and P15 are fed from supply voltage V_{DDPA}.*

3.17 Clock Generation

The Clock Generation Unit can generate the system clock signal f_{SYS} for the XC226xN from a number of external or internal clock sources:

- External clock signals with pad voltage or core voltage levels
- External crystal or resonator using the on-chip oscillator
- On-chip clock source for operation without crystal/resonator
- Wake-up clock (ultra-low-power) to further reduce power consumption

The programmable on-chip PLL with multiple prescalers generates a clock signal for maximum system performance from standard crystals, a clock input signal, or from the on-chip clock source. See also **Section 4.7.2**.

The Oscillator Watchdog (OWD) generates an interrupt if the crystal oscillator frequency falls below a certain limit or stops completely. In this case, the system can be supplied with an emergency clock to enable operation even after an external clock failure.

All available clock signals can be output on one of two selectable pins.

3.20 Instruction Set Summary

Table 11 lists the instructions of the XC226xN.
The addressing modes that can be used with a specific instruction, the function of the instructions, parameters for conditional execution of instructions, and the opcodes for each instruction can be found in the **“Instruction Set Manual”**.

This document also provides a detailed description of each instruction.

Table 11 Instruction Set Summary

Mnemonic	Description	Bytes
ADD(B)	Add word (byte) operands	2 / 4
ADDC(B)	Add word (byte) operands with Carry	2 / 4
SUB(B)	Subtract word (byte) operands	2 / 4
SUBC(B)	Subtract word (byte) operands with Carry	2 / 4
MUL(U)	(Un)Signed multiply direct GPR by direct GPR (16- × 16-bit)	2
DIV(U)	(Un)Signed divide register MDL by direct GPR (16-/16-bit)	2
DIVL(U)	(Un)Signed long divide reg. MD by direct GPR (32-/16-bit)	2
CPL(B)	Complement direct word (byte) GPR	2
NEG(B)	Negate direct word (byte) GPR	2
AND(B)	Bitwise AND, (word/byte operands)	2 / 4
OR(B)	Bitwise OR, (word/byte operands)	2 / 4
XOR(B)	Bitwise exclusive OR, (word/byte operands)	2 / 4
BCLR/BSET	Clear/Set direct bit	2
BMOV(N)	Move (negated) direct bit to direct bit	4
BAND/BOR/BXOR	AND/OR/XOR direct bit with direct bit	4
BCMP	Compare direct bit to direct bit	4
BFLDH/BFLDL	Bitwise modify masked high/low byte of bit-addressable direct word memory with immediate data	4
CMP(B)	Compare word (byte) operands	2 / 4
CMPD1/2	Compare word data to GPR and decrement GPR by 1/2	2 / 4
CMPI1/2	Compare word data to GPR and increment GPR by 1/2	2 / 4
PRIOR	Determine number of shift cycles to normalize direct word GPR and store result in direct word GPR	2
SHL/SHR	Shift left/right direct word GPR	2

4.4 Analog/Digital Converter Parameters

These parameters describe the conditions for optimum ADC performance.

Note: Operating Conditions apply.

Table 20 ADC Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Switched capacitance at an analog input	C_{AINSW} CC	–	–	4	pF	not subject to production test [1]
Total capacitance at an analog input	C_{AINT} CC	–	–	10	pF	not subject to production test [1]
Switched capacitance at the reference input	C_{AREFSW} CC	–	–	7	pF	not subject to production test [1]
Total capacitance at the reference input	C_{AREFT} CC	–	–	15	pF	not subject to production test [1]
Differential Non-Linearity Error	$\lvert EA_{DNL}\rvert$ CC	–	0.8	1	LSB	
Gain Error	$\lvert EA_{GAIN}\rvert$ CC	–	0.4	0.8	LSB	
Integral Non-Linearity	$\lvert EA_{INL}\rvert$ CC	–	0.8	1.2	LSB	
Offset Error	$\lvert EA_{OFF}\rvert$ CC	–	0.5	0.8	LSB	
Analog clock frequency	f_{ADCI} SR	0.5	–	16.5	MHz	voltage_range= lower
		0.5	–	20	MHz	voltage_range= upper
Input resistance of the selected analog channel	R_{AIN} CC	–	–	2	kOhm	not subject to production test [1]
Input resistance of the reference input	R_{AREF} CC	–	–	2	kOhm	not subject to production test [1]

Table 20 ADC Parameters (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Broken wire detection delay against VAGND[2]	t_{BWG} CC	–	–	50[3]		
Broken wire detection delay against VAREF[2]	t_{BWR} CC	–	–	50[4]		
Conversion time for 8-bit result[2]	t_{c8} CC	(11+STC) x t_{ADCI} + 2 x t_{SYS}	–	–		
Conversion time for 10-bit result[2]	t_{c10} CC	(13+STC) x t_{ADCI} + 2 x t_{SYS}	–	–		
Total Unadjusted Error	|TUE| CC	–	1	2	LSB	[5]
Wakeup time from analog powerdown, fast mode	t_{WAF} CC	–	–	4	µs	
Wakeup time from analog powerdown, slow mode	t_{WAS} CC	–	–	15	µs	
Analog reference ground	V_{AGND} SR	V_{SS} - 0.05	–	1.5	V	
Analog input voltage range	V_{AIN} SR	V_{AGND}	–	V_{AREF}	V	[6]
Analog reference voltage	V_{AREF} SR	V_{AGND} + 1.0	–	V_{DDPA} + 0.05	V	

1) These parameter values cover the complete operating range. Under relaxed operating conditions (temperature, supply voltage) typical values can be used for calculation. At room temperature and nominal supply voltage the following typical values can be used: $C_{AINTtyp}$ = 12 pF, $C_{AINStyp}$ = 5 pF, R_{AINtyp} = 1.0 kOhm, $C_{AREFTtyp}$ = 15 pF, $C_{AREFStyp}$ = 10 pF, $R_{AREFtyp}$ = 1.0 kOhm.

2) This parameter includes the sample time (also the additional sample time specified by STC), the time to determine the digital result and the time to load the result register with the conversion result. Values for the basic clock t_{ADCI} depend on programming.

3) The broken wire detection delay against V_{AGND} is measured in numbers of consecutive precharge cycles at a conversion rate of not more than 500 µs. Result below 10% (66_H)

4.6 Flash Memory Parameters

The XC226xN is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XC226xN's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 25 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	2[1]		$N_{FL\_RD} \leq 1$
		–	–	1[2]		$N_{FL\_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq$ 20 years
Flash wait states[3]	$N_{WSFLASH}$ SR	1	–	–		$f_{SYS} \leq$ 8 MHz
		2	–	–		$f_{SYS} \leq$ 13 MHz
		3	–	–		$f_{SYS} \leq$ 17 MHz
		4	–	–		$f_{SYS} >$ 17 MHz
Erase time per sector/page	t_{ER} CC	–	7[4]	8.0	ms	
Programming time per page	t_{PR} CC	–	3[4]	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{ER} \leq$ 1,000 cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	
Number of erase cycles	N_{ER} SR	–	–	15.000	cycles	$t_{RET} \geq$ 5 years; Valid for Flash module 1 (up to 64 kbytes)
		–	–	1.000	cycles	$t_{RET} \geq$ 20 years

1) The unused Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

2) Flash module 1 can be erased/programmed while code is executed and/or data is read from Flash module 0.
3) Value of IMB_IMBCTRL.WSFLASH.
4) Programming and erase times depend on the internal Flash clock source. The control state machine needs a few system clock cycles. This increases the stated durations noticably only at extremely low system clock frequencies.

Access to the XC226xN Flash modules is controlled by the IMB. Built-in prefetch mechanisms optimize the performance for sequential access.

Flash access waitstates only affect non-sequential access. Due to prefetch mechanisms, the performance for sequential access (depending on the software structure) is only partially influenced by waitstates.

The timing in the AC Characteristics refers to TCSs. Timing must be calculated using the minimum TCS possible under the given circumstances.
The actual minimum value for TCS depends on the jitter of the PLL. Because the PLL is constantly adjusting its output frequency to correspond to the input frequency (from crystal or oscillator), the accumulated jitter is limited. This means that the relative deviation for periods of more than one TCS is lower than for a single TCS (see formulas and **Figure 20**).

This is especially important for bus cycles using waitstates and for the operation of timers, serial interfaces, etc. For all slower operations and longer periods (e.g. pulse train generation or measurement, lower baudrates, etc.) the deviation caused by the PLL jitter is negligible.

The value of the accumulated PLL jitter depends on the number of consecutive VCO output cycles within the respective timeframe. The VCO output clock is divided by the output prescaler K2 to generate the system clock signal f_{SYS}. The number of VCO cycles is K2 × **T**, where **T** is the number of consecutive f_{SYS} cycles (TCS).

The maximum accumulated jitter (long-term jitter) D_{Tmax} is defined by:

D_{Tmax} [ns] = ±(220 / (K2 × f_{SYS}) + 4.3)

This maximum value is applicable, if either the number of clock cycles T > (f_{SYS} / 1.2) or the prescaler value K2 > 17.

In all other cases for a timeframe of **T** × TCS the accumulated jitter D_T is determined by:

D_T [ns] = D_{Tmax} × [(1 - 0.058 × K2) × (T - 1) / (0.83 × f_{SYS} - 1) + 0.058 × K2]

f_{SYS} in [MHz] in all formulas.

Example, for a period of 3 TCSs @ 33 MHz and K2 = 4:

D_{max} = ±(220 / (4 × 33) + 4.3) = 5.97 ns (Not applicable directly in this case!)

D_3 = 5.97 × [(1 - 0.058 × 4) × (3 - 1) / (0.83 × 33 - 1) + 0.058 × 4]
= 5.97 × [0.768 × 2 / 26.39 + 0.232]
= 1.7 ns

Example, for a period of 3 TCSs @ 33 MHz and K2 = 2:

D_{max} = ±(220 / (2 × 33) + 4.3) = 7.63 ns (Not applicable directly in this case!)

D_3 = 7.63 × [(1 - 0.058 × 2) × (3 - 1) / (0.83 × 33 - 1) + 0.058 × 2]
= 7.63 × [0.884 × 2 / 26.39 + 0.116]
= 1.4 ns

1) The amplitude voltage V_{AX1} refers to the offset voltage V_{OFF}. This offset voltage must be stable during the operation and the resulting voltage peaks must remain within the limits defined by V_{IX1}.
2) Overload conditions must not occur on pin XTAL1.

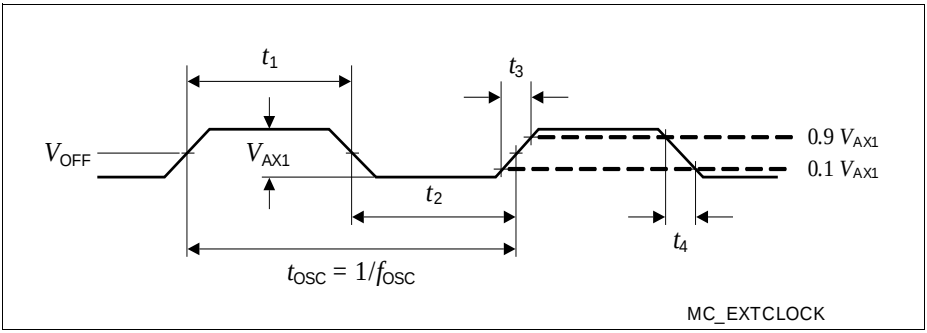

Figure 21 External Clock Drive XTAL1

Note: For crystal or ceramic resonator operation, it is strongly recommended to measure the oscillation allowance (negative resistance) in the final target system (layout) to determine the optimum parameters for oscillator operation.
The manufacturers of crystals and ceramic resonators offer an oscillator evaluation service. This evaluation checks the crystal/resonator specification limits to ensure a reliable oscillator operation.

Table 29 Standard Pad Parameters for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Rise and Fall times (10% - 90%)	t_{RF} CC	–	–	37 + 0.65 x C_L	ns	$C_L \geq$ 20 pF; $C_L \leq$ 100 pF; Driver_Strength = Medium
		–	–	24 + 0.3 x C_L	ns	$C_L \geq$ 20 pF; $C_L \leq$ 100 pF; Driver_Strength = Strong ; Driver_Edge= Medium
		–	–	6.2 + 0.24 x C_L	ns	$C_L \geq$ 20 pF; $C_L \leq$ 100 pF; Driver_Strength = Strong ; Driver_Edge= Sharp
		–	–	34 + 0.3 x C_L	ns	$C_L \geq$ 20 pF; $C_L \leq$ 100 pF; Driver_Strength = Strong ; Driver_Edge= Slow
		–	–	500 + 2.5 x C_L	ns	$C_L \geq$ 20 pF; $C_L \leq$ 100 pF; Driver_Strength = Weak

1) An output current above $|I_{OXnom}|$ may be drawn from up to three pins at the same time. For any group of 16 neighboring output pins, the total output current in each direction (ΣI_{OL} and Σ-I_{OH}) must remain below 50 mA.

Table 33 External Bus Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output valid delay for $\overline{RD}$, $\overline{WR}$(L/$\overline{H}$)	t_{10} CC	–	11	20	ns	
Output valid delay for $\overline{BHE}$, ALE	t_{11} CC	–	10	21	ns	
Address output valid delay for A23 ... A0	t_{12} CC	–	11	22	ns	
Address output valid delay for AD15 ... AD0 (MUX mode)	t_{13} CC	–	10	22	ns	
Output valid delay for $\overline{CS}$	t_{14} CC	–	10	13	ns	
Data output valid delay for AD15 ... AD0 (write data, MUX mode)	t_{15} CC	–	10	22	ns	
Data output valid delay for D15 ... D0 (write data, DEMUX mode)	t_{16} CC	–	10	22	ns	
Output hold time for $\overline{RD}$, $\overline{WR}$(L/$\overline{H}$)	t_{20} CC	-2	8	10	ns	
Output hold time for $\overline{BHE}$, ALE	t_{21} CC	-2	8	10	ns	
Address output hold time for AD15 ... AD0	t_{23} CC	-3	8	10	ns	
Output hold time for $\overline{CS}$	t_{24} CC	-3	8	11	ns	
Data output hold time for D15 ... D0 and AD15 ... AD0	t_{25} CC	-3	8	10	ns	
Input setup time for READY, D15 ... D0, AD15 ... AD0	t_{30} SR	29	17	–	ns	
Input hold time READY, D15 ... D0, AD15 ... AD0[1)]	t_{31} SR	0	-9	–	ns	

1) Read data are latched with the same internal clock edge that triggers the address change and the rising edge of RD. Address changes before the end of RD have no impact on (demultiplexed) read cycles. Read data can change after the rising edge of RD.

Note: If the READY input is sampled inactive at the indicated sampling point (“Not Rdy”) a READY-controlled waitstate is inserted (tpRDY),
sampling the READY input active at the indicated sampling point (“Ready”) terminates the currently running bus cycle.
Note the different sampling points for synchronous and asynchronous READY.
This example uses one mandatory waitstate (see tpE) before the READY input value is used.

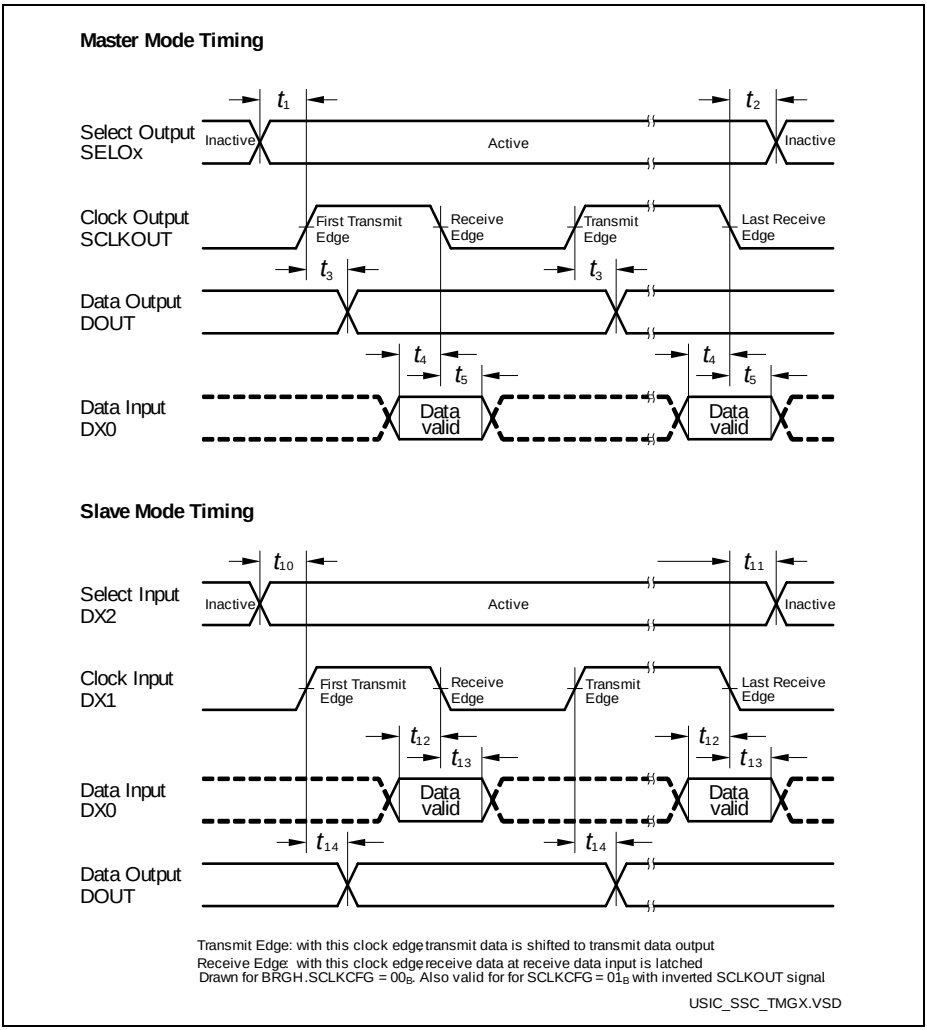

Figure 26 USIC - SSC Master/Slave Mode Timing

Note: This timing diagram shows a standard configuration where the slave select signal is low-active and the serial clock signal is not shifted and not inverted.

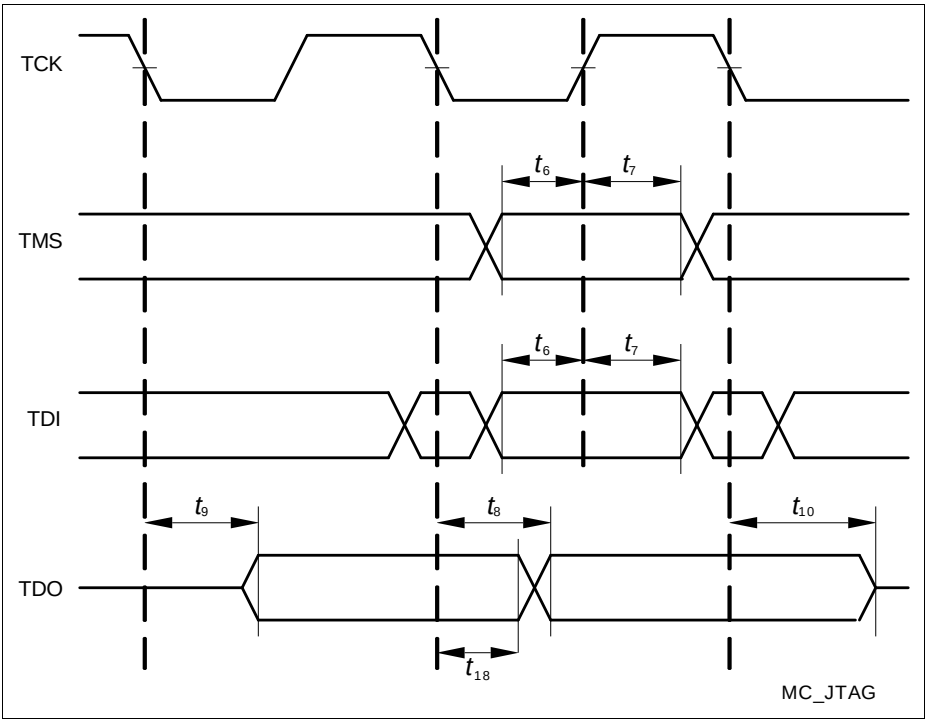

Figure 31 JTAG Timing